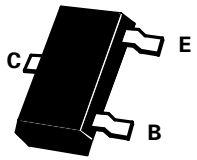
SOT23 PNP SILICON PLANAR HIGH VOLTAGE TRANSISTOR

HT3

ISSUE 2 - SEPTEMBER 1995 ✪

PARTMARKING DETAIL - 3T



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-90	V
Collector-Emitter Voltage	V_{CEO}	-80	V
Emitter-Base Voltage	V_{EBO}	-5	V
Continuous Collector Current	I_C	-100	mA
Power Dissipation at T_{amb} = 25°C	P_{tot}	330	mW
Operating and Storage Temperature Range	T_j:T_{stg}	-55 to +150	°C

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-90		V	I_C=-10μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-80		V	I_C=-2mA
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5		V	I_E=-10μA
Collector Cut-Off Current	I_{CBO}		-100	nA	V_{CB}=-80V, I_E=0
	I_{CES}		-100 -5	nA μA	V_{CE}=-80V, V_{BE}=0 V_{CE}=-80V, V_{BE}=0 T_j=125°C
	I_{CEX}		-10	μA	V_{CE}=-80V,V_{BE}=-0.2V, T_j=85°C
Emitter Cut-Off Current	I_{EBO}		-200	nA	V_{EB}=-4V
Static Forward Current Transfer Ratio	h_{FE}	30 35 50 30			I_C=-100μA, V_{CE}=-1V I_C=-1mA, V_{CE}=-1V I_C=-10mA, V_{CE}=-1V I_C=-50mA, V_{CE}=-1V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-750	mV	I_C=-50mA, I_B=-5mA
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-1.1	V	I_C=-50mA, I_B=-5mA
Output Capacitance	C_{obo}		10	pF	V_{CB}=-10V, I_E=0, f=1MHz
Transition Frequency	f_T	50		MHz	I_C=-10mA, V_{CE}=-5V f=10MHz
Switching Times	t_{on} t_{off}		500 1000	ns ns	I_C=-10ma, I_{B1} = I_{B2} = -1ma